

Silicon PNP Power Transistors

2SA1060

DESCRIPTION

- With TO-3PN package
- Complement to type 2SC2484
- High collector power dissipation

APPLICATIONS

- High power audio frequency amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

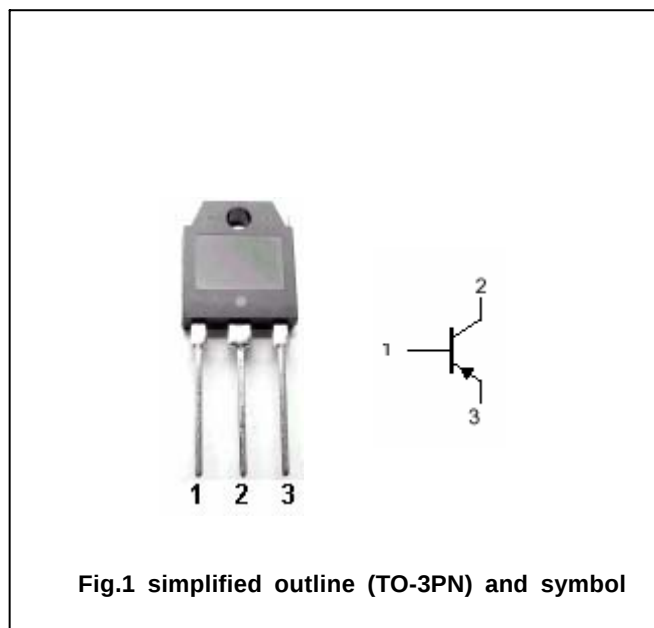


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings ($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-80	V
V_{CEO}	Collector-emitter voltage	Open base	-80	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-5	A
I_{CM}	Collector current-peak		-8	A
P_C	Collector power dissipation	$T_C=25$	60	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-10mA ; I_B=0$	-80			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3A ; I_B=-0.3A$			-2.0	V
V_{BE}	Base-emitter on voltage	$I_C=-3A ; V_{CE}=-5V$			-1.8	V
I_{CBO}	Collector cut-off current	$V_{CB}=-80V ; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3V ; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-20mA ; V_{CE}=-5V$	20			
h_{FE-2}	DC current gain	$I_C=-1A ; V_{CE}=-5V$	40		200	
h_{FE-3}	DC current gain	$I_C=-3A ; V_{CE}=-5V$	20			
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-5V$		20		MHz

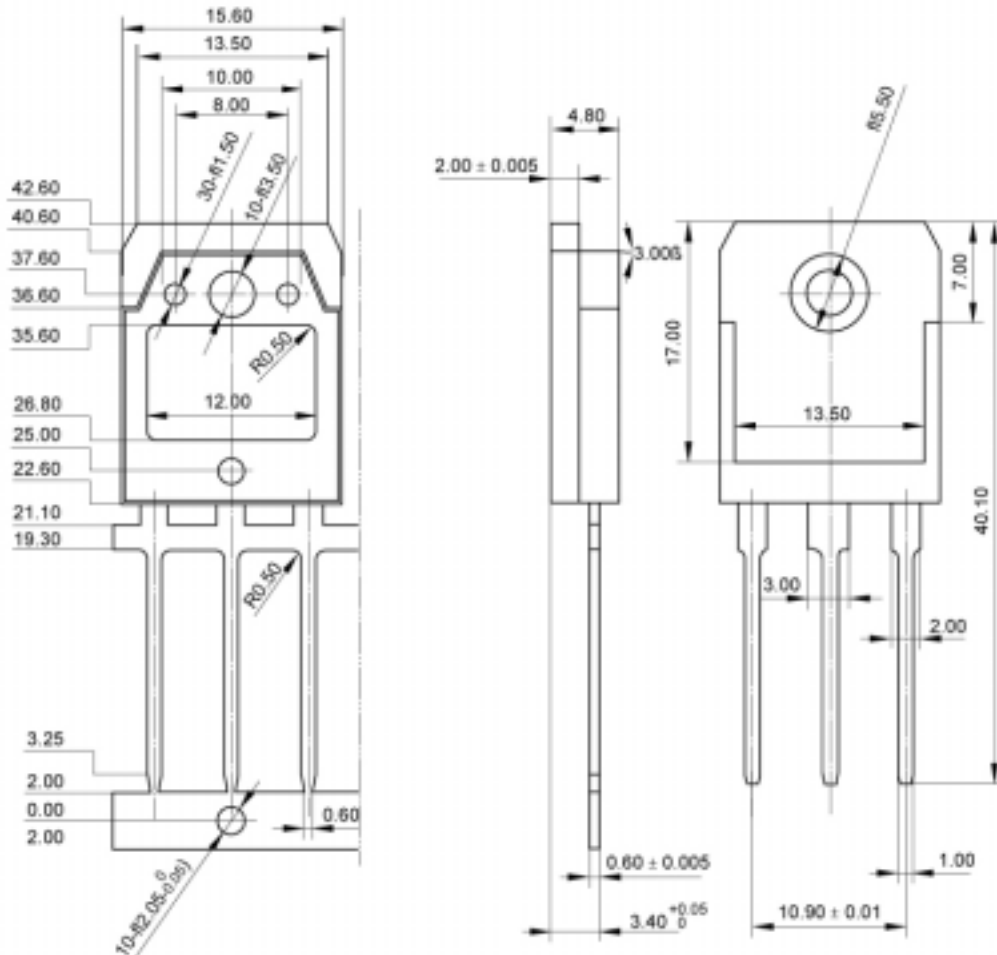
◆ h_{FE-2} Classifications

R	Q	P
40-80	60-120	100-200

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.10\text{mm}$)